Product data sheet

1. General description

Planar passivated high commutation three quadrant triac in a SOT186A "full pack" plastic package intended for use in circuits where high static and dynamic dV/dt and high dl/dt can occur. This "series C" triac will commutate the full rated RMS current at the maximum rated junction temperature without the aid of a snubber.

2. Features and benefits

- 3Q technology for improved noise immunity
- High commutation capability with maximum false trigger immunity
- High immunity to false turn-on by dV/dt
- High voltage capability
- Isolated mounting base package
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only

3. Applications

- Electronic thermostats
- High power motor controls e.g. washing machines and vacuum cleaners
- · Rectifier-fed DC inductive loads e.g. DC motors and solenoids
- Refrigeration and air conditioning compressors

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------------|--|---|-----|-----|-----|------|
| V_{DRM} | repetitive peak off- state voltage | | - | - | 800 | V |
| I _{TSM} | non-repetitive peak on- state current | full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig. 4; Fig. 5 | - | - | 140 | Α |
| I _{T(RMS)} | RMS on-state current | full sine wave; $T_h \le 45$ °C; Fig. 1; Fig. 2; Fig. 3 | - | - | 16 | Α |
| Static characte | eristics | | | | | |
| I _{GT} | gate trigger current | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$ | 2 | - | 35 | mA |





| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|--------|-----------|--|-----|-----|-----|------|
| | | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 7$ | 2 | - | 35 | mA |
| | | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{}$ | 2 | - | 35 | mA |

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------------------|--------------------|----------------|
| 1 | T1 | main terminal 1 | mb | T2—T1 |
| 2 | T2 | main terminal 2 | | G sym051 |
| 3 | G | gate | | · |
| mb | n.c. | mounting base; isolated | | |
| | | | TO-220F (SOT186A) | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | | | | | | |
|------------------|---------|---|---------|--|--|--|--|--|
| | Name | Description | Version | | | | | |
| BTA316X-800C | TO-220F | plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack" | SOT186A | | | | | |
| BTA316X-800C/L01 | TO-220F | plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack" | SOT186A | | | | | |

7. Marking

Table 4. Marking codes

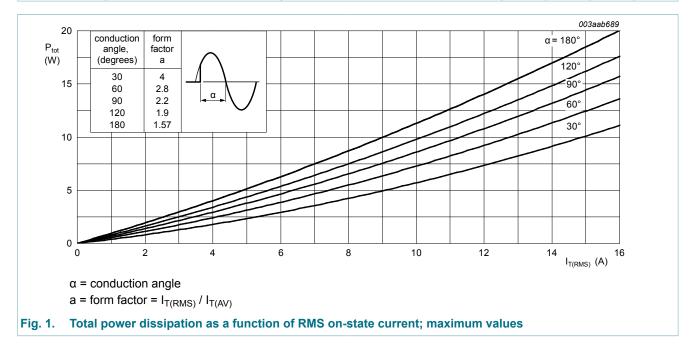
| Type number | Marking code |
|------------------|--------------|
| BTA316X-800C | BTA316X-800C |
| BTA316X-800C/L01 | |

8. Limiting values

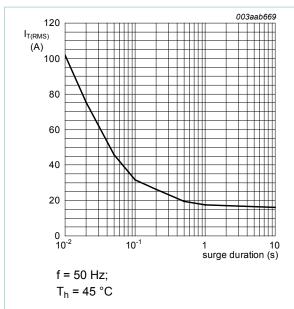
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|---------------------|--------------------------------------|--|-----|-----|------------------|
| V_{DRM} | repetitive peak off-state voltage | | - | 800 | V |
| I _{T(RMS)} | RMS on-state current | full sine wave; $T_h \le 45$ °C; Fig. 1; Fig. 2; Fig. 3 | - | 16 | А |
| I _{TSM} | non-repetitive peak on-state current | full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; $Fig. 4$; $Fig. 5$ | - | 140 | А |
| | | full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$ | - | 150 | А |
| l ² t | I ² t for fusing | t _p = 10 ms; SIN | - | 98 | A ² s |
| dI _T /dt | rate of rise of on-state current | $I_T = 20 \text{ A}; I_G = 0.2 \text{ A}; dI_G/dt = 0.2 \text{ A/}\mu\text{s}$ | - | 100 | A/µs |
| I _{GM} | peak gate current | | - | 2 | Α |
| P_{GM} | peak gate power | | - | 5 | W |
| P _{G(AV)} | average gate power | over any 20 ms period | - | 0.5 | W |
| T _{stg} | storage temperature | | -40 | 150 | °C |
| T _j | junction temperature | | - | 125 | °C |



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20 003aab667 I_{T(RMS)} (A) 16 12 8 4 4 0 0 50 100 T_h (°C) 150

Fig. 3. RMS on-state current as a function of heatsink temperature; maximum values

Fig. 2. RMS on-state current as a function of surge duration; maximum values

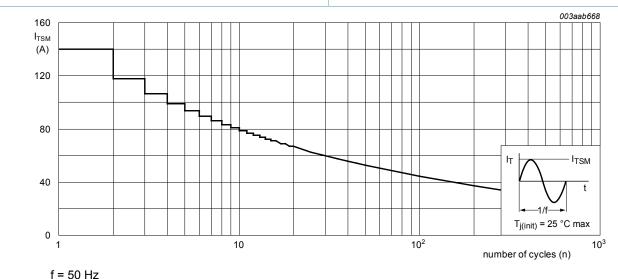
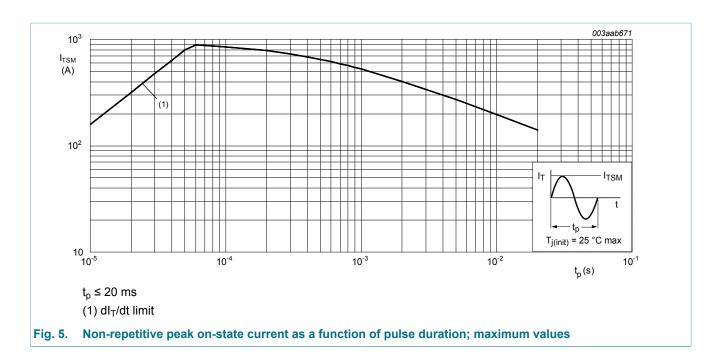


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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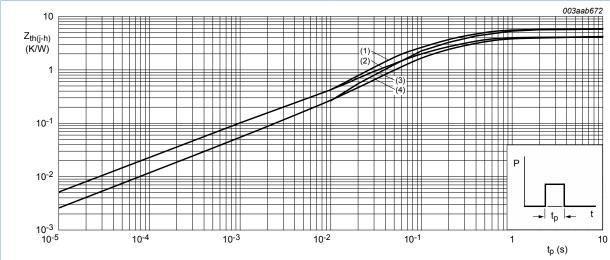


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9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---|---|---|-----|-----|-----|------|
| R _{th(j-h)} thermal resistance from junction to heatsink | | full cycle or half cycle; with heatsink compound; Fig. 6 | - | - | 4 | K/W |
| | | full cycle or half cycle; without heatsink compound; Fig. 6 | - | - | 5.5 | K/W |
| R _{th(j-a)} | thermal resistance from junction to ambient | in free air | _ | 55 | - | K/W |



- (1) Unidirectional (half cycle) without heatsink compound
- (2) Unidirectional (half cycle) with heatsink compound
- (3) Bidirectional (full cycle) without heatsink compound
- (4) Bidirectional (full cycle) with heatsink compound

Fig. 6. Transient thermal impedance from junction to heatsink as a function of pulse duration

10. Isolation characteristics

Table 7. Isolation characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|------------------------|-----------------------|--|-----|-----|------|------|
| V _{isol(RMS)} | RMS isolation voltage | from all terminals to external heatsink; sinusoidal waveform; clean and dust free; 50 Hz \leq f \leq 60 Hz; RH \leq 65 %; T _h = 25 °C | - | - | 2500 | V |
| C _{isol} | isolation capacitance | from main terminal 2 to external heatsink; f = 1 MHz; T _h = 25 °C | - | 10 | - | pF |

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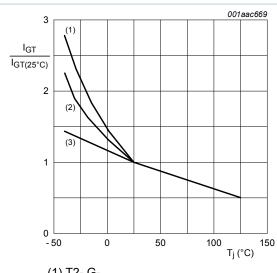
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11. Characteristics

Table 8. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------------|---------------------------------------|---|------|-----|------|------|
| Static char | acteristics | | | | | |
| I _{GT} | gate trigger current | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$ | 2 | - | 35 | mA |
| | | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ \text{ G-;}$ $T_j = 25 \text{ °C; } \underline{\text{Fig. 7}}$ | 2 | - | 35 | mA |
| | | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } Fig. 7$ | 2 | - | 35 | mA |
| IL | latching current | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$ | - | - | 50 | mA |
| | | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 8$ | - | - | 60 | mA |
| | | $V_D = 12 \text{ V; } I_G = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } \underline{\text{Fig. 8}}$ | - | - | 50 | mA |
| I _H | holding current | V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u> | - | - | 35 | mA |
| V _T | on-state voltage | I _T = 18 A; T _j = 25 °C; <u>Fig. 10</u> | - | 1.3 | 1.5 | V |
| V_{GT} | gate trigger voltage | V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; Fig. 11 | - | 0.8 | 1 | V |
| | | V _D = 400 V; I _T = 0.1 A; T _j = 125 °C; Fig. 11 | 0.25 | 0.4 | - | V |
| I _D | off-state current | V _D = 800 V; T _j = 125 °C | - | 0.1 | 0.5 | mA |
| Dynamic cl | naracteristics | | | | | |
| dV _D /dt | rate of rise of off-state voltage | V_{DM} = 535 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit | 500 | - | - | V/µs |
| dl _{com} /dt | rate of change of commutating current | V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 16 A; dV_{com}/dt = 20 V/ μ s; (snubberless condition); gate open circuit | - | - | A/ms | |

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- (1) T2- G-
- (2) T2+ G-
- (3) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

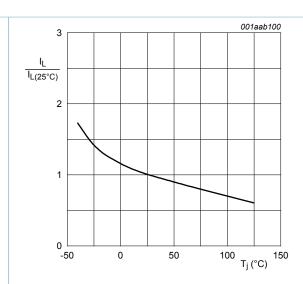


Fig. 8. Normalized latching current as a function of junction temperature

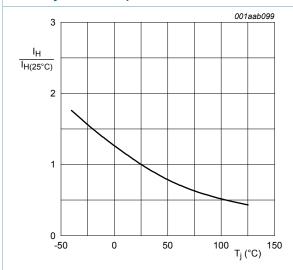
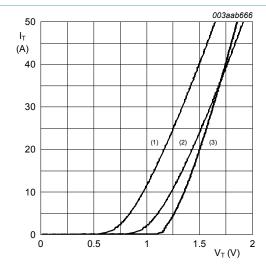


Fig. 9. Normalized holding current as a function of junction temperature



 V_o = 1.024 V; R_s = 0.021 Ω

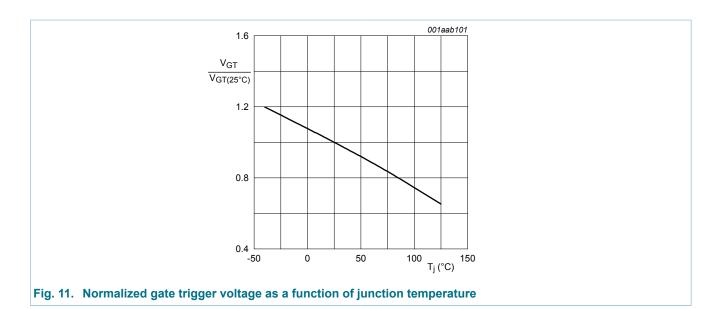
(1) T_i = 125 °C; typical values

(2) T_i = 125 °C; maximum values

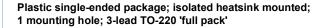
(3) T_i = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

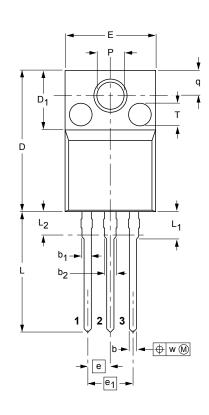
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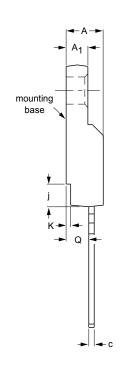


12. Package outline



SOT186A





0 5 10 mm

DIMENSIONS (mm are the original dimensions)

| UN | т | A | A ₁ | b | b ₁ | b ₂ | С | D | D ₁ | E | е | e ₁ | j | к | L | L ₁ | L ₂ ⁽¹⁾ max. | Р | Q | q | T ⁽²⁾ | w |
|----|----------|----|----------------|------------|----------------|----------------|------------|--------------|----------------|-------------|------|----------------|------------|------------|--------------|----------------|---------------------------------------|------------|------------|------------|------------------|-----|
| mr | 1 4 4 | .6 | 2.9 2.5 | 0.9 0.7 | 1.1 0.9 | 1.4 1.0 | 0.7 0.4 | 15.8 15.2 | 6.5 6.3 | 10.3 9.7 | 2.54 | 5.08 | 2.7 1.7 | 0.6 0.4 | 14.4 13.5 | 3.30 2.79 | 3 | 3.2 3.0 | 2.6 2.3 | 3.0 2.6 | 2.5 | 0.4 |

Notes

- 1. Terminal dimensions within this zone are uncontrolled.
- 2. Both recesses are # 2.5×0.8 max. depth

| OUTLINE | | EUROPEAN | ISSUE DATE | | | |
|---------|-----|----------------|------------|--|------------|----------------------------------|
| VERSION | IEC | JEDEC | JEITA | | PROJECTION | ISSUE DATE |
| SOT186A | | 3-lead TO-220F | | | | -02-04-09 06-02-14 |

Fig. 12. Package outline TO-220F (SOT186A)

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